



# STB95NF03

## N-CHANNEL 30V - 0.0065 Ω - 95A D<sup>2</sup>PAK STripFET™ II POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB95NF03	30 V	<0.007 Ω	80 A

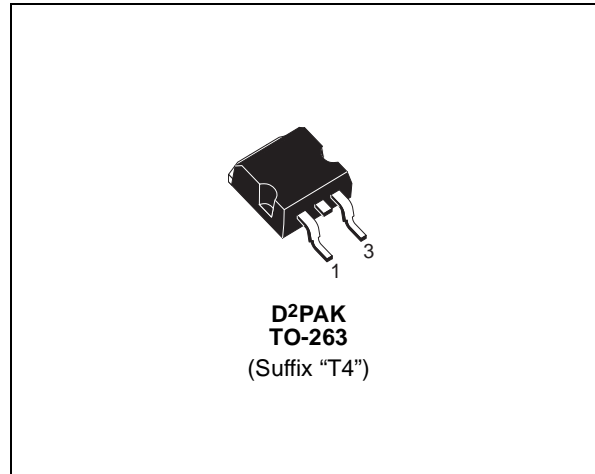
- TYPICAL R<sub>DS(on)</sub> = 0.0065 Ω
- STANDARD THRESHOLD DRIVE
- 100% AVALANCHE TESTED
- SURFACE-MOUNTING D<sup>2</sup>PAK (TO-263)  
POWER PACKAGE IN TUBE (NO SUFFIX) OR  
IN TAPE & REEL (SUFFIX "T4")

### DESCRIPTION

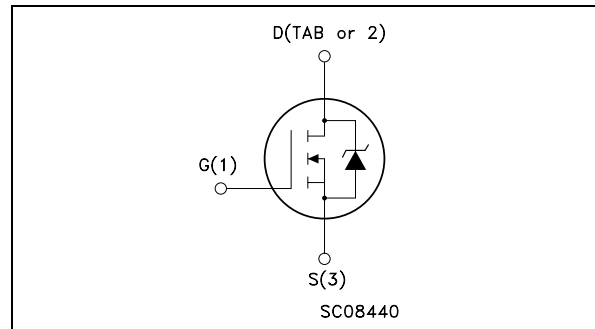
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- DC-DC & DC-AC CONVERTERS
- SOLENOID AND RELAY DRIVERS



### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	30	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	30	V
V <sub>GS</sub>	Gate- source Voltage	± 20	V
I <sub>D</sub> (*)	Drain Current (continuous) at T <sub>C</sub> = 25°C	80	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	80	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	320	A
P <sub>tot</sub>	Total Dissipation at T <sub>C</sub> = 25°C	150	W
	Derating Factor	1	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	3.0	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	720	mJ
T <sub>stg</sub>	Storage Temperature	-55 to 175	°C
T <sub>j</sub>	Operating Junction Temperature		

(•) Pulse width limited by safe operating area.  
(\* ) Current Limited by Package

(1) I<sub>SD</sub> ≤ 95A, di/dt ≤ 150A/μs, V<sub>DD</sub> ≤ V(BR)DSS, T<sub>j</sub> ≤ T<sub>JMAX</sub>.  
(2) Starting T<sub>j</sub> = 25 °C, I<sub>D</sub> = 47.5A, V<sub>DD</sub> = 25V

**THERMAL DATA**

Rthj-case	Thermal Resistance Junction-case	Max	1	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300	°C

**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>C</sub> = 125°C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			±100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2		4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 45 A		0.0065	0.0070	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> = 15 V I <sub>D</sub> = 45 A		50		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V f = 1 MHz V <sub>GS</sub> = 0		2450		pF
C <sub>oss</sub>	Output Capacitance			880		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			170		pF

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## ELECTRICAL CHARACTERISTICS (continued)

### SWITCHING ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Time Rise Time	$V_{DD} = 15\text{ V}$ $I_D = 47.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		20 195		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD}=15\text{ V}$ $I_D=95\text{ A}$ $V_{GS}=10\text{ V}$		59 18 21	70	nC nC nC

### SWITCHING OFF(\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off Delay Time Fall Time	$V_{DD} = 20\text{ V}$ $I_D = 47.5\text{ A}$ $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$		35 35		ns ns

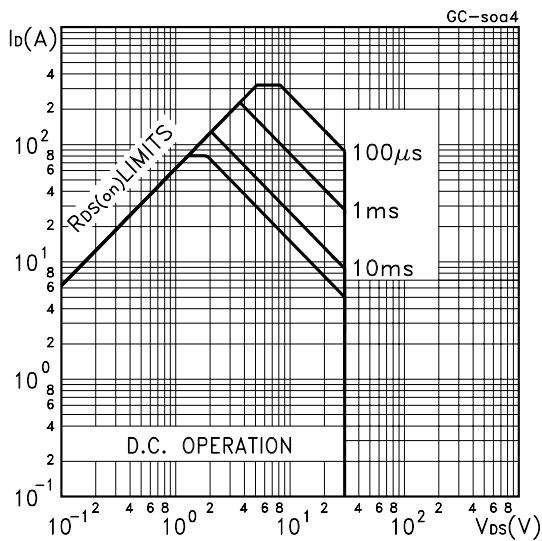
### SOURCE DRAIN DIODE(\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM} (*)$	Source-drain Current Source-drain Current (pulsed)				95 320	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 95\text{ A}$ $V_{GS} = 0$			1.3	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 95\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		60 120 4		ns nC A

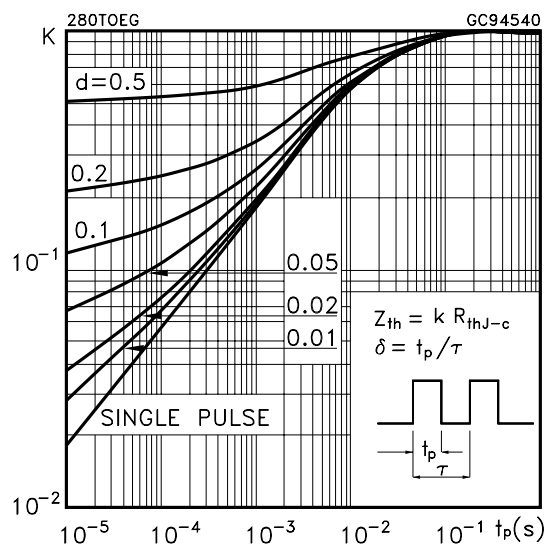
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

(\*) Pulse width limited by  $T_{jmax}$

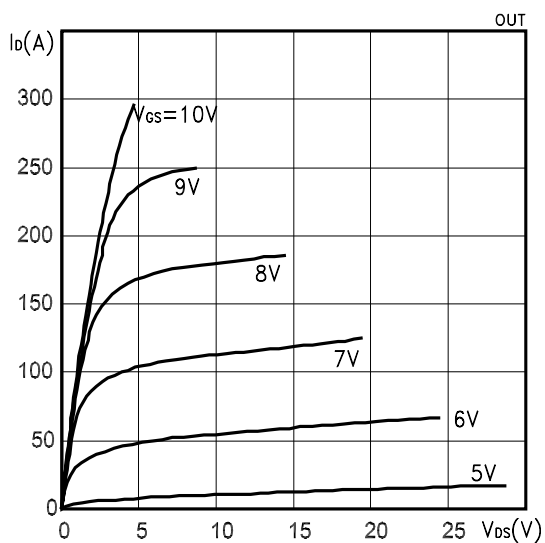
### Safe Operating Area



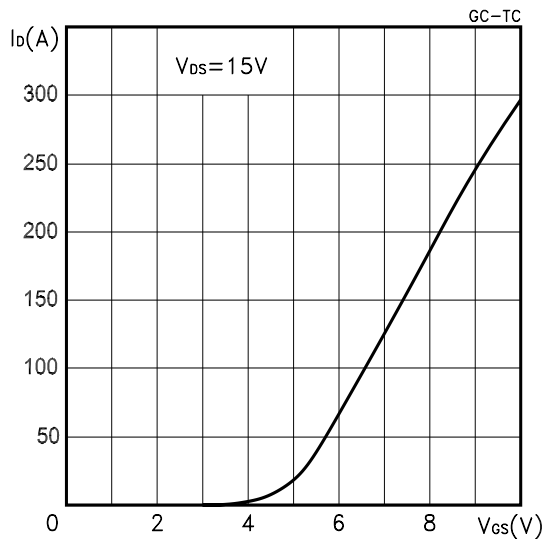
### Thermal Impedance



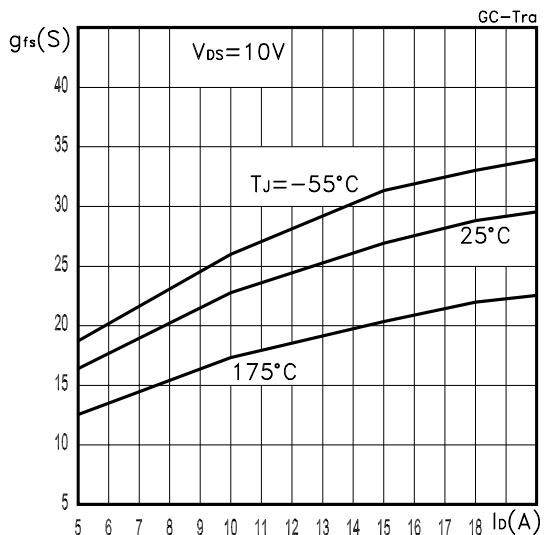
Output Characteristics



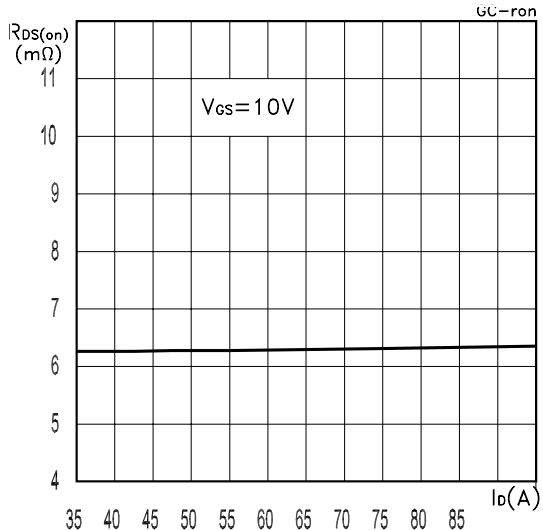
Transfer Characteristics



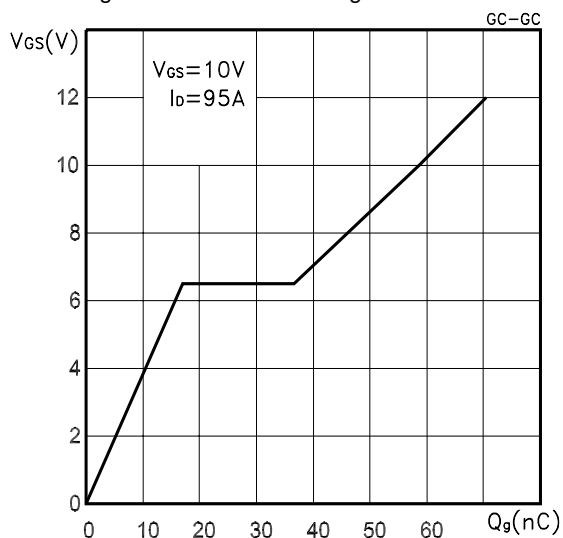
Transconductance



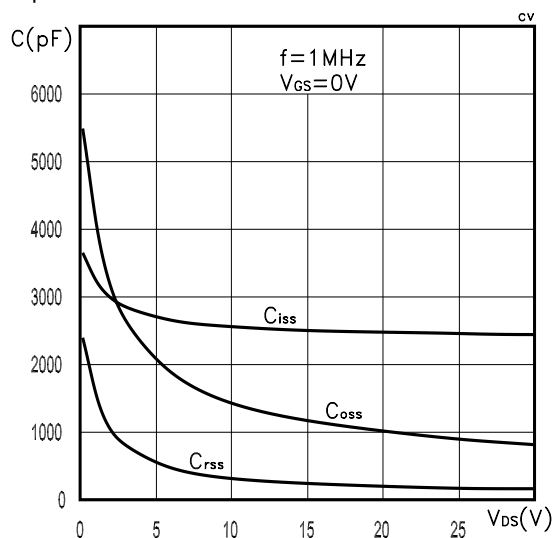
Static Drain-source On Resistance



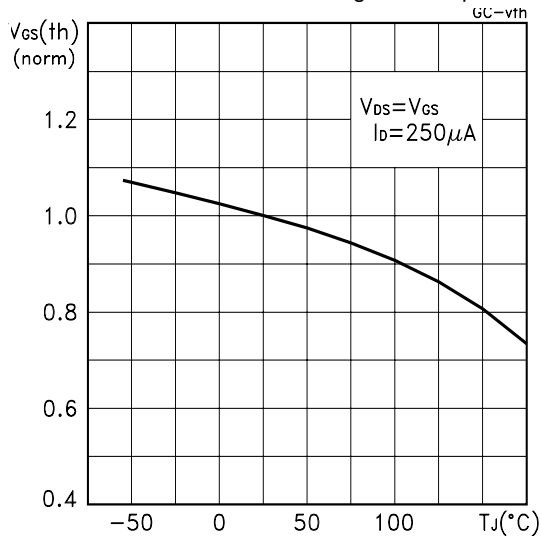
Gate Charge vs Gate-source Voltage



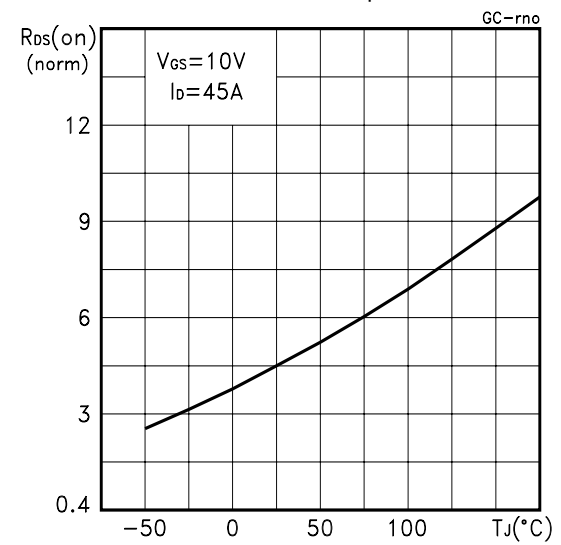
Capacitance Variations



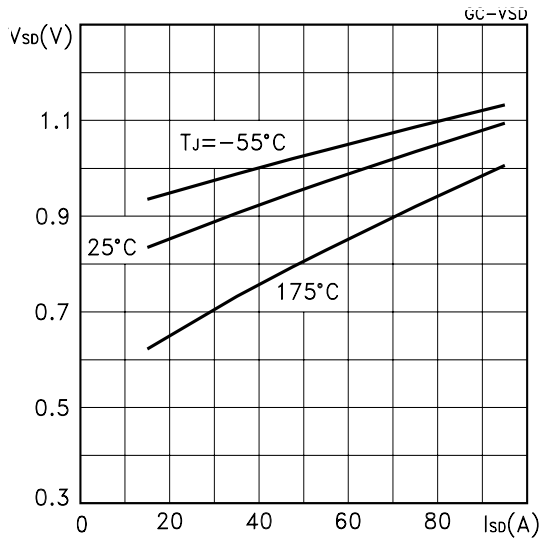
Normalized Gate Threshold Voltage vs Temperature



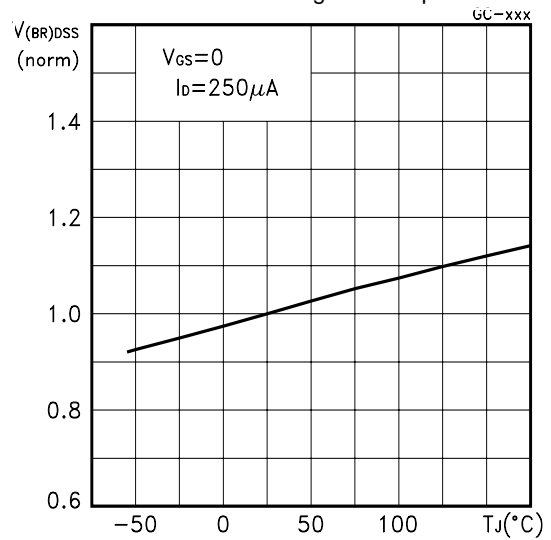
Normalized on Resistance vs Temperature



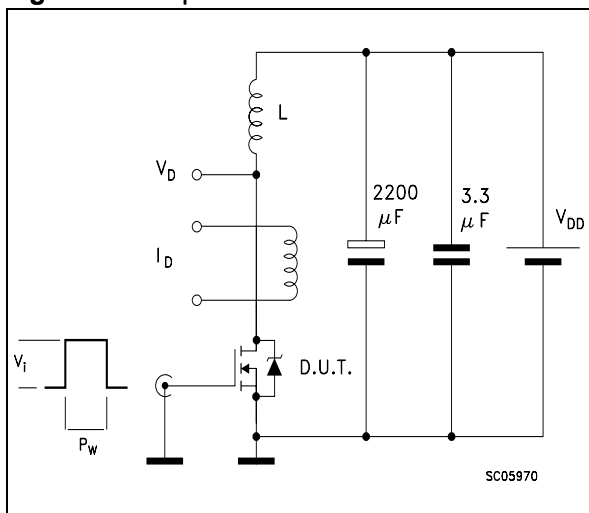
Source-drain Diode Forward Characteristics



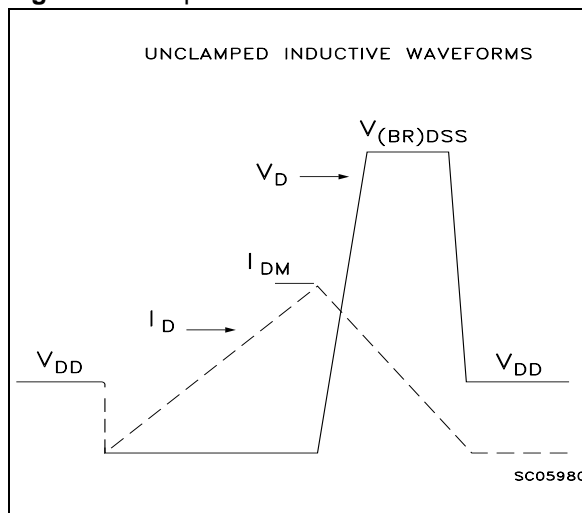
Normalized Breakdown Voltage vs Temperature.



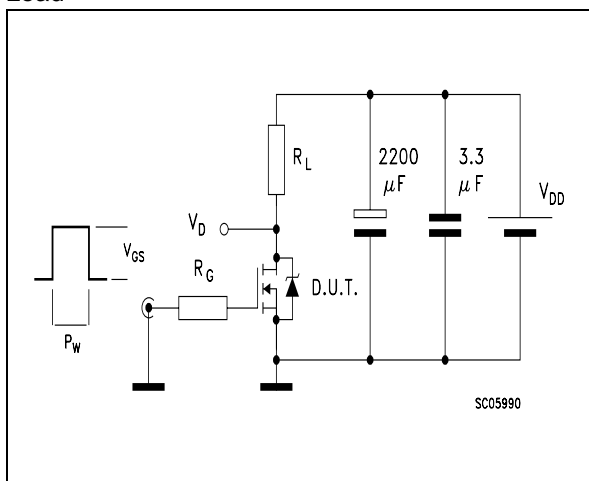
**Fig. 1: Unclamped Inductive Load Test Circuit**



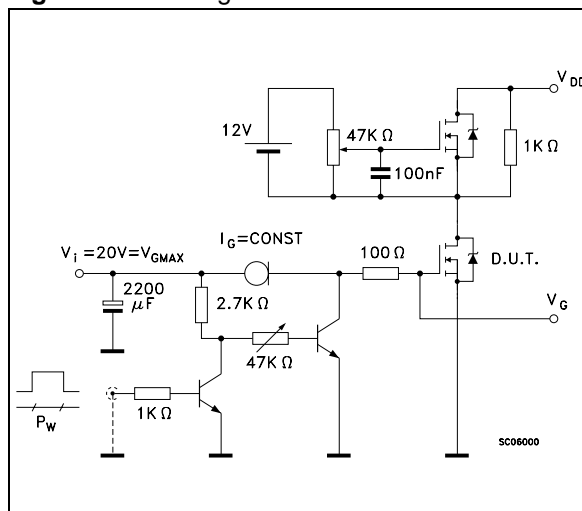
**Fig. 2: Unclamped Inductive Waveform**



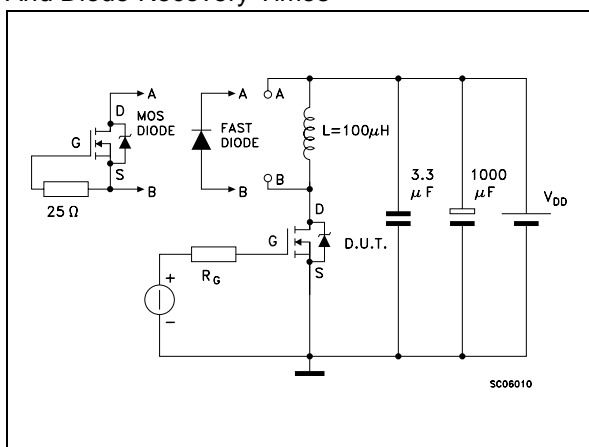
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

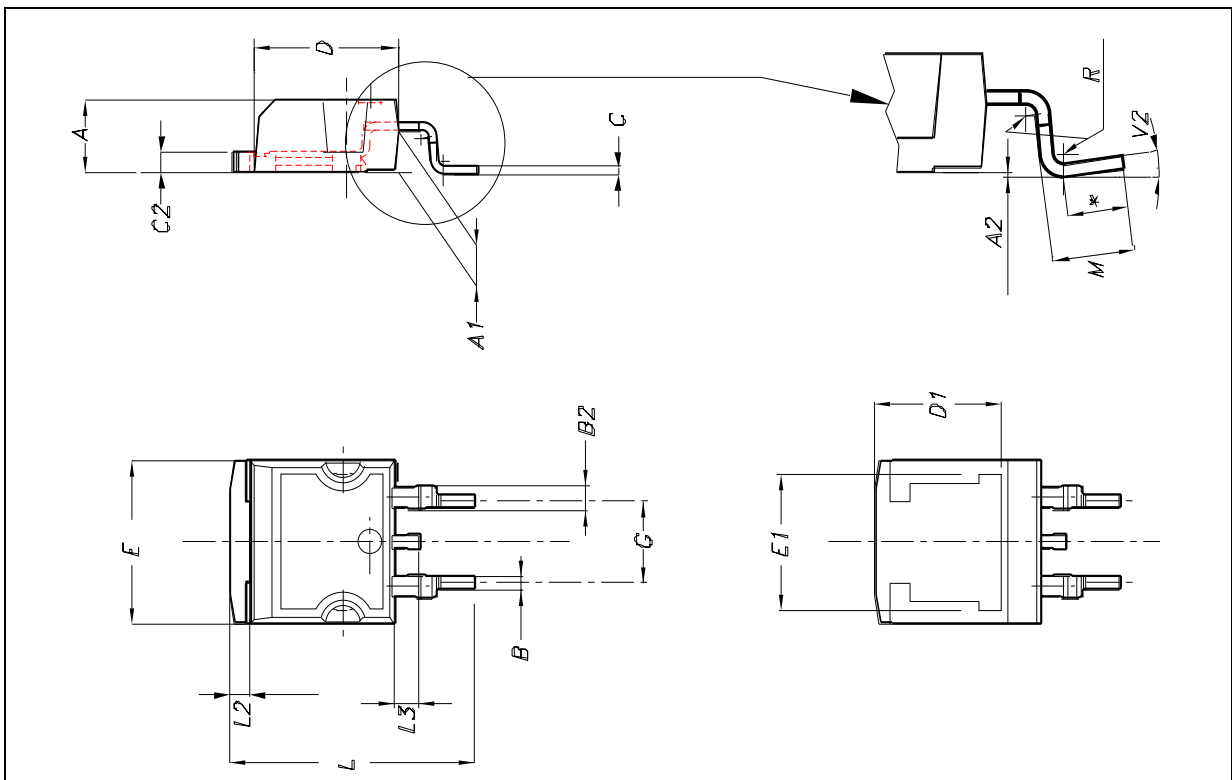


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**

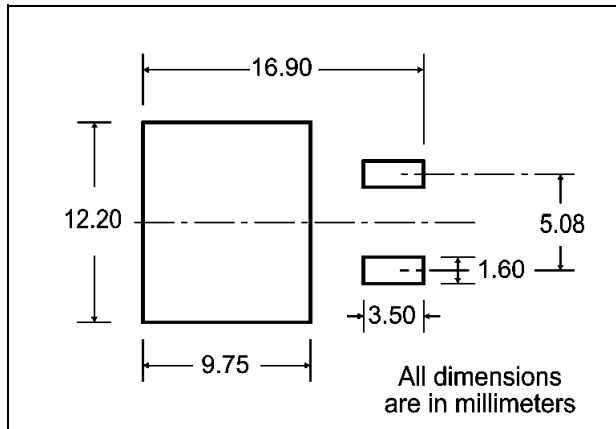


**D<sup>2</sup>PAK MECHANICAL DATA**

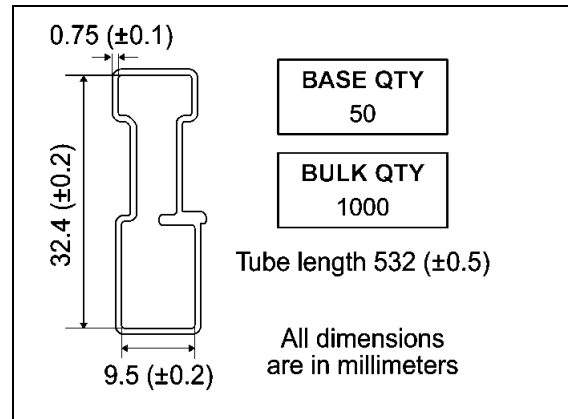
DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°	0°		8°



**D2PAK FOOTPRINT**



**TUBE SHIPMENT (no suffix)\***



**TAPE AND REEL SHIPMENT (suffix "T4")\***

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius R min.

\* on sales type



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